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| U.S. Department of Commerce, Patent and Trademark Office | | | | | | Atty Docket No. | | Serial No. | |
| | | | | | | M-12336 US | | 10/02/696 | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | | | | | Applicant(s) | | | |
| (Use several sheets if necessary) | | | | | | Daniel C. Guterman et al. | | | |
| | | | | | | Filing Date | | Group | |
| | | | | | | October 31, 2001 | | 2812 | |
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| | | Document | Date | Country | Class | Subclass | Yes | No | |
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| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant. | | | | | | | | | |

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| | | Document | Date | Country | Class | Subclass | Yes | No | |
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| | | | | | | | | Translation | |
| | | Document | Date | Country | Class | Subclass | Yes | No | |
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